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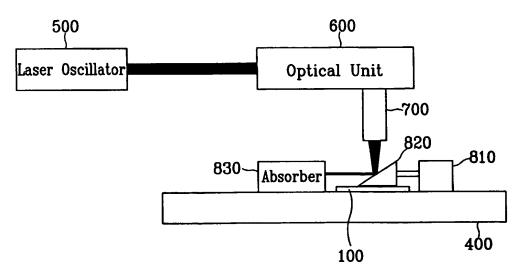
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(54) Title: METHOD OF POLYCYRSTALLIZATION, METHOD OF MANUFACTURING POLYSILICON THIN FILM TRAN-SISTOR, AND LASER IRRADIATION DEVICE THEREFOR



(57) Abstract: A device for irradiating a laser beam onto an amorphous silicon thin film formed on a substrate. The device includes: a stage mounting the substrate; a laser oscillator for generating a laser beam; a projection lens for focusing and guiding the laser beam onto the thin film; a reflector for reflecting the laser beam guided onto the thin film; a controller for controlling a position of the reflector; and an absorber for absorbing the laser beam reflected by the reflector.

